

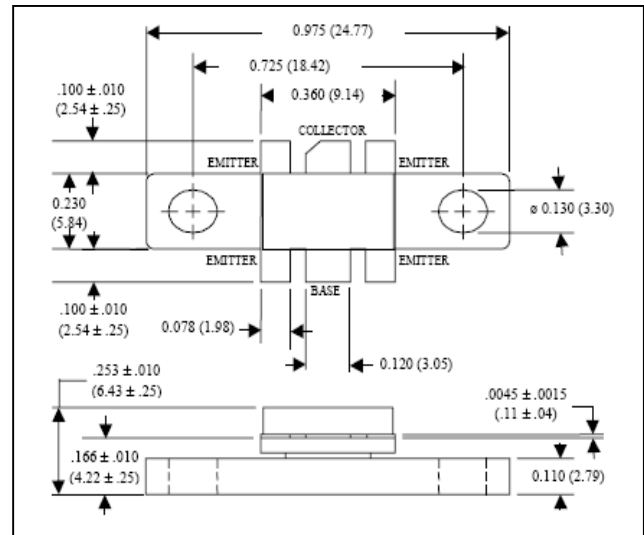
Wireless Power Transistor 15W, 850-960MHz, 26V

M/A-COM Products
Released - Rev. 07.07

Features

- Designed for linear amplifier applications
- Class AB: -30 dBc typ. 3rd IMD at 15 W PEP
- Common emitter configuration
- Internal input impedance matching
- Diffused emitter ballasting

Outline Drawing¹



Notes: (unless otherwise specified)

1. Tolerances are: inches ± .005" (millimeters ± 0.13mm)

ABSOLUTE MAXIMUM RATING AT 25°C

Parameter	Symbol	Rating	Units
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CES}	60	V
Emitter-Base Voltage	V_{EBO}	3.0	V
Collector Current	I_C	1.8	A
Dissipation @ 25°C	P_D	43	W
Storage Temperature	T_{stg}	-55 to +150	°C
Junction Temperature	T_j	200	°C
Thermal Resistance	θ_{j_c}	3.5	°C/W

ELECTRICAL SPECIFICATIONS AT 25°C

Symbol	Parameter	Test Conditions	Min	Max	Units
BV_{CES}	Collector-Emitter Breakdown	$I_C=15mA$	60	-	V
I_{CES}	Collector-Emitter Leakage	$V_{CE}=24.0 V$	-	2.0	mA
BV_{CEO}	Collector-Emitter Breakdown	$I_C=40 mA$	24	-	V
BV_{EBO}	Emitter-Base Breakdown	$I_B=2.5 mA$	3.0	-	V
h_{FE}	DC Forward Current Gain	$V_{CE}=5.0 V, I_C=0.5 A$	15	120	-
G_P	Power Gain	$V_{CC}=24 V, I_{CQ}=100 mA, P_{out}=15W, f=900 MHz$	12	-	dB
η	Collector Efficiency	$V_{CC}=24 V, I_{CQ}=100 mA, P_{out}=15W, f=900 MHz$	50	-	%
R_L	Input Return Loss	$V_{CC}=24 V, I_{CQ}=100 mA, P_{out}=15W, f=900 MHz$	10	-	dB
VSWR	Load Mismatch Tolerance	$V_{CC}=24 V, I_{CQ}=100 mA, P_{out}=15W PEP, f=900 MHz, \Delta f=100 kHz$	-	10:1	-
IMD ₃	3rd Order IMD	$V_{CC}=24 V, I_{CQ}=100 mA, P_{out}=15W PEP, f=900 MHz, \Delta f=100 kHz$	-	-30	dBc

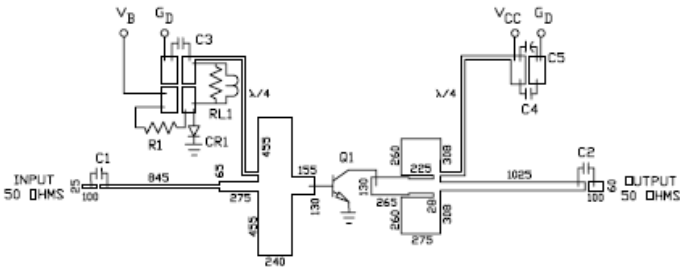
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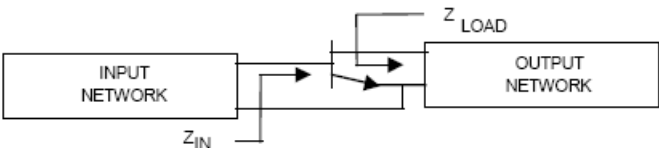
ELECTRICAL SCHEMATIC



Notes:
1. Dimensions are in mils.

ELECTRICAL SCHEMATIC PARTS LIST

C1, C2, C3	100 pF ATC Size A
C4	5000 pF ATC Size B
C5	50 uF 50 Volts
CR1	Diode cathode tied to flange (Harris 1N4245)
Q1	PH0810-15
R1	5 Ohms ¼ W
RL1	10T / No. 22 AWG on 3.1 Ohm ¼ Watt
Board Type	Rogers 6010.5 .025" thick, E _R = 10.5



TYPICAL OPTIMUM DEVICE IMPEDANCE

F (MHz)	Z _{in} (Ω)	Z _{load} (Ω)
850	2.5 + j3.6	4.3 + j2.6
900	2.9 + j2.4	4.4 + j3.4
960	1.5 + j2.0	4.3 + j3.9